Amendments to the Claims:

This listing of claims will replace all prior versions, and listings, of claims in the application:

Listing of Claims:

1-20 (canceled).

21. (New): A method for manufacturing a semiconductor device comprising:

forming a MISFET having a first-conductivity type semiconductor substrate; an insulating film formed on said semiconductor substrate; a gate electrode formed on said semiconductor substrate via said insulating film; a second-conductivity type source/drain region formed on both sides of a channel forming region located under said gate electrode formed on said semiconductor substrate via said insulating film; a thickness of said insulating film being less than 2.5nm at a silicon oxide equivalent thickness; and a gate length of said gate electrode being equal to or less than 0.3 μm, in a part of an area of said semiconductor substrate;

wherein said method comprises:

forming a thick insulating film on a surface of said semiconductor substrate by a furnace oxidation method;

removing the thick insulating film at said part of an area; and

forming a thin insulating film of less than 2.5nm at a silicon oxide equivalent thickness at said part of an area by a rapid thermal process.

22. (New): The method for manufacturing a semiconductor device according to claim 21,

wherein said part of an area includes a corner of the semiconductor substrate.

23. (New): The method for manufacturing a semiconductor device according to claim 21, wherein said part of an area includes an outer portion of the semiconductor substrate.

24. (New): The method for manufacturing a semiconductor device according to claim 21,

wherein said thin insulating film is an oxide film and said oxide film is formed by a rapid thermal oxidation (RTO) method at said part of an area.

25. (New): The method for manufacturing a semiconductor device according to claim 24,

wherein a channel direction length (Lg) of said gate electrode and a thickness (Tox) of said oxide film are determined by the following relationship;

$Lg \leq 10^{(Tox-2.02)}$

where a unit of Lg is μm.

26. (New): The method for manufacturing a semiconductor device according to claim 25,

wherein the thickness (Tox) of said oxide film is less than 2.5 nm.

27. (New): The method for manufacturing a semiconductor device according to claim 25,

wherein the thickness (Tox) of said oxide film is equal to or less than 2.0 nm.

28. (New): The method for manufacturing a semiconductor device according to claim 24,

wherein a channel direction length (Lg) of said gate electrode and a thickness (Tox) of said oxide film are determined by the following relationship;

$Lg \leq 10^{(Tox-2.32)}$

where a unit of Lg is μm.

29. (New): The method for manufacturing a semiconductor device according to claim 28,

wherein the thickness (Tox) of said oxide film is less than 2.5 nm.

30. (New): The method for manufacturing a semiconductor device according to claim 28,

wherein the thickness (Tox) of said oxide film is equal to or less than 2.0 nm.

31. (New): A method for manufacturing a semiconductor device comprising:

forming a MOSFET having a first-conductivity type semiconductor substrate; an oxide film formed on said semiconductor substrate; a gate electrode formed on said semiconductor substrate via said oxide film; a second-conductivity type source/drain region formed on both sides of a channel forming region located under said gate electrode formed on said semiconductor substrate via said oxide film; and a channel direction length (Lg) of said gate electrode and a thickness (Tox) of said oxide film are determined by the following relationship;

$Lg \leq 10^{(Tox-2.02)}$

where a unit of Lg is μm, in a part of an area of said semiconductor substrate;

wherein said method comprises:

forming a thick oxide film on a surface of said semiconductor substrate by a furnace oxidation method;

removing the thick oxide film at said part of an area; and

forming a thin oxide film of less than 2.5nm at said part of an area by a rapid thermal oxidation (RTO) method.

32. (New): The method for manufacturing a semiconductor device according to claim 31,

wherein said part of an area includes a corner of the semiconductor substrate.

33. (New): The method for manufacturing a semiconductor device according to claim 31, wherein said part includes an outer portion of the semiconductor substrate.

34. (New): The method for manufacturing a semiconductor device according to claim 31,

wherein the thickness (Tox) of said thin oxide film is equal to or less than 2.0 nm.

35. (New): The method for manufacturing a semiconductor device according to claim 31,

wherein a channel direction length (Lg) of said gate electrode and a thickness (Tox) of said thin oxide film are determined by the following relationship;

$Lg \leq 10^{(Tox-2.32)}$

where a unit of Lg is μm.

36. (New): The method for manufacturing a semiconductor device according to claim 35,

wherein the thickness (Tox) of said thin oxide film is equal to or less than 2.0 nm.